

Intense upconversion and infrared emissions in $\text{Er}^{3+}\text{-Yb}^{3+}$ codoped Lu_2SiO_5 and $(\text{Lu}_{0.5}\text{Gd}_{0.5})_2\text{SiO}_5$ crystals

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High optical quality Lu_2SiO_5 (LSO) and $(\text{Lu}_{0.5}\text{Gd}_{0.5})_2\text{SiO}_5$ (LGSO) laser crystals codoped with Er^{3+} and Yb^{3+} have been fabricated by the Czochralski method. Intense upconversion (UC) and infrared emission (1543 nm) are observed under excitation of 975 nm. The luminescence processes are explained and the emission efficiencies are quantitatively obtained by measuring the UC efficiency and calculating the emission cross section. The temperature-dependent optical properties of the crystals are also investigated. Our study indicates that $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LSO}$ and $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LGSO}$ crystals are promising gain media for developing the solid-state 1.5 μm optical amplifiers and tunable UC lasers. © 2008 American Institute of Physics. [DOI: 10.1063/1.2954010]

Er^{3+} doped materials have been attracting intensive research attention for their excellent performance in upconversion (UC) and near infrared (NIR, near 1.5 μm) emission.¹⁻³ It is well known that different host materials significantly affect the emission performance of the rare-earth ions, thus considerable research effort has been spent on investigating efficient hosts. Silicate crystals have been actively investigated recently as the photoluminescence material because of their low symmetry, high quantum efficiency, and superior luminescence properties. Remarkable luminescence and laser performance have been achieved in Yb^{3+} doped Gd_2SiO_5 (GSO), Lu_2SiO_5 (LSO), Y_2SiO_5 (YSO), and $\text{Er}^{3+}\text{-Yb}^{3+}$ codoped GSO crystals.⁴⁻⁶

In this letter, we present the fabrication, luminescence and thermal properties of $\text{Er}^{3+}\text{-Yb}^{3+}$ codoped LSO and $(\text{Lu}_{0.5}\text{Gd}_{0.5})_2\text{SiO}_5$ (LGSO) crystals. LSO and LGSO crystals have been studied exclusively as the scintillator materials doped with Ce^{3+} and they have not yet been investigated as the luminescence or laser material when codoped with Er^{3+} and Yb^{3+} . Our study shows that $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LSO}$ and $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LGSO}$ crystals present not only intense visible UC but also good NIR emission under 975 nm excitation. Their UC efficiencies can be compared to those of fluoride glass. Meanwhile, highly efficient NIR emission at 1543 nm are also obtained over a wide temperature range.

LSO and LGSO single crystals codoped with Er^{3+} and Yb^{3+} have been grown by the Czochralski method. The parameters are listed in Table I. The luminescence spectra were obtained using a fluorescence spectrophotometer (model F111AI) under the 975 nm laser diode (LD) excitation. The UC emission efficiencies were measured by bandpass filter and power meter. The temperature of the crystal is controlled from 260 to 470 K through a copper sample mount, which can be heated by a resistance wire element and cooled by a thermoelectric cooler. A copper-constantan thermocouple is attached to one facet of the crystal sample to monitor the temperature within an accuracy of 0.5 °C.

TABLE I. Physical parameters of $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LSO}$ and $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LGSO}$.

Sample	Concentration ($\times 10^{20}/\text{cm}^3$)		Thickness (mm)	Density (g/cm^3)	
	Er^{3+}	Yb^{3+}			
LSO	0.868	28.9	0.74	7.4	
LGSO	0.867	28.9	0.76	7.1	
	Refractive Index		Space	Group	E_{phonon}
LSO	1.82		C2/c		970 cm^{-1}
LGSO	1.80		C2/c		1194 cm^{-1}

Figure 1 shows the UC emission spectra of $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LSO}$ and $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LGSO}$ at 300 K when the pump power of the 975 nm LD is fixed at 278 mW. Green and red emission bands of these two crystals are clearly observed, and their emission bands are very broad with multiple peaks. The UC efficiencies were measured and the normalized UC efficiency η_{up} are listed in Table II. The values in LSO and LGSO crystals are higher than those in tellurite, phosphate, and silicate glasses, and comparable to those in

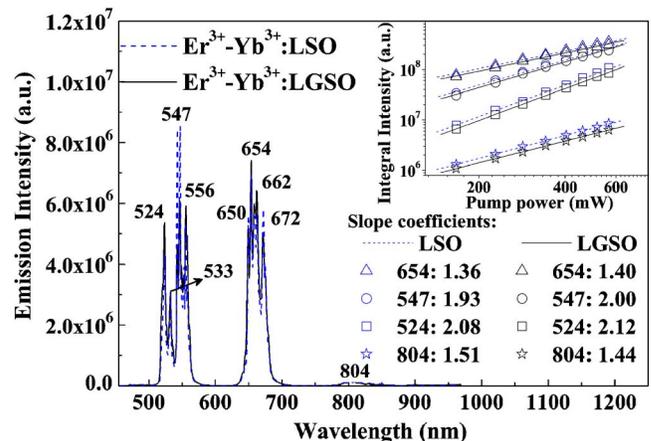


FIG. 1. (Color online) UC spectra of $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LSO}$ and $\text{Er}^{3+}\text{-Yb}^{3+}\text{:LGSO}$ at 300 K under 975 nm LD excitation. Inset is log-log plots of the integrated emission intensities vs the excitation power.

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TABLE III. Emission cross sections (σ_{em}) of Er^{3+} ($^4I_{13/2} \rightarrow ^4I_{15/2}$) in different host materials.

	LSO ^a	LGSO ^a	YSO ^b	GSO ^b	YCOB ^b	YAG ^b	Tellurite ^c	Phosphate ^d	AYF ^e
σ_{em} ($\times 10^{-20}$ cm ²)	0.793	0.994	0.8	1.03	0.6	1.5	0.852	0.78	0.549

^aOur work.^bReference 10.^cReference 8.^dReference 11.^eReference 12.

can be explained from two aspects. First, as the temperature increases, nonradiative MPR rates are enhanced to weaken the radiative transitions at the same level. Secondly, the improved MPR processes also shorten the lifetimes of some of the middle energy levels involved in the UC process ($^4I_{11/2}$ and $^4I_{13/2}$), thus reduce the possibility of the photon absorption that follows. As for the 524 nm signal, the major reason for the intensity to increase slightly as the temperature grows should be attributed to the enhanced population at $^2H_{11/2}$ level via MPR process. It is to be noted that because the thermal distribution of the population between $^4S_{3/2}$ and $^2H_{11/2}$ is very sensitive to temperature, the emission intensity of 524 nm is not very stable, especially for LSO.

In the NIR emission, the consistent increasing of the intensity near 1543 nm as the temperature grows can be explained as the following. First of all, the main depopulating mechanism of $^4I_{13/2}$ level is the ion-ion interactions [(d)–(f) in Fig. 2] because the MPR process from $^4I_{13/2}$ to the ground level can be neglected due to its large energy separation. Thus, the depopulation rate of $^4I_{13/2}$ level only depends on the ion concentration. At the same time, the MPR processes from the upper levels populating the $^4I_{13/2}$ level are enhanced as the temperature increases, resulting in an improved emis-

sion rate from the $^4I_{13/2}$ level to the ground state.

To summarize, strong UC and NIR emissions are demonstrated in $Er^{3+}-Yb^{3+}$:LSO and $Er^{3+}-Yb^{3+}$:LGSO crystals under 975 nm excitation. Their normalized UC efficiencies can reach up to 0.89×10^{-3} (LSO, green), 1.04×10^{-3} (LSO, red), 0.83×10^{-3} (LGSO, green), and 0.93×10^{-3} (LGSO, red). Meanwhile, highly efficient NIR emission at 1543 nm ($\sigma_{em,LSO} \geq 0.793 \times 10^{-20}$ cm², $\sigma_{em,LGSO} \geq 0.994 \times 10^{-20}$ cm²) are also obtained over a wide temperature range (300–470 K). These results indicate that $Er^{3+}-Yb^{3+}$:LSO and $Er^{3+}-Yb^{3+}$:LGSO crystals are good candidates as the gain medium for solid-state optical amplifiers at 1.5 μ m as well as tunable UC lasers.

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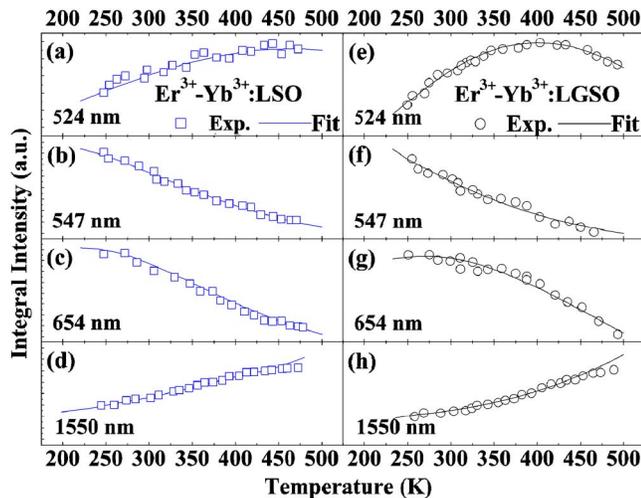


FIG. 4. (Color online) Temperature evolution of the experimental intensities and theoretical fitting results. The pump power of 975 nm LD is fixed at 278 mW. [(a)–(d)] $Er^{3+}-Yb^{3+}$:LSO, and [(e)–(h)] $Er^{3+}-Yb^{3+}$:LGSO.

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